

LM146/LM346 Programmable Quad Operational Amplifiers

Check for Samples: [LM146](#), [LM346](#)

FEATURES

- ($I_{SET}=10 \mu A$)
- **Programmable Electrical Characteristics**
- **Battery-Powered Operation**
- **Low Supply Current: 350 μA /Amplifier**
- **Ensured Gain Bandwidth Product: 0.8 MHz Min**
- **Large DC Voltage Gain: 120 dB**
- **Low Noise Voltage: 28 nV/ \sqrt{Hz}**
- **Wide Power Supply Range: $\pm 1.5V$ to $\pm 22V$**
- **Class AB Output Stage—No Crossover Distortion**
- **Ideal Pin Out for Biquad Active Filters**
- **Input Bias Currents are Temperature Compensated**

Connection Diagram

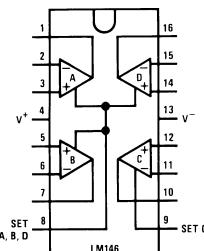


Figure 1. Dual-In-Line Package - Top View
See Package Number NFE0016A, D0016A or N16A

PROGRAMMING EQUATIONS

Total Supply Current = 1.4 mA ($I_{SET}/10 \mu A$)

Gain Bandwidth Product = 1 MHz ($I_{SET}/10 \mu A$)

Slew Rate = 0.4V/ μs ($I_{SET}/10 \mu A$)

Input Bias Current $\approx 50 nA$ ($I_{SET}/10 \mu A$)

I_{SET} = Current into pin 8, pin 9 (see [Schematic Diagram](#))

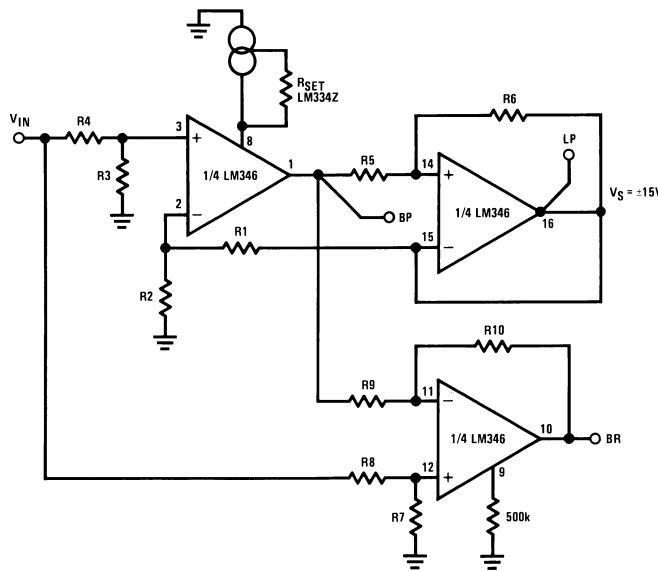
$$I_{SET} = \frac{V^+ - V^- - 0.6V}{R_{SET}} \quad (1)$$



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Capacitorless Active Filters (Basic Circuit)



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ABSOLUTE MAXIMUM RATINGS⁽¹⁾⁽²⁾⁽³⁾

		LM146	LM346
Supply Voltage		$\pm 22V$	$\pm 18V$
Differential Input Voltage ⁽²⁾		$\pm 30V$	$\pm 30V$
CM Input Voltage ⁽²⁾		$\pm 15V$	$\pm 15V$
Power Dissipation ⁽⁴⁾		900 mW	500 mW
Output Short-Circuit Duration ⁽⁵⁾		Continuous	Continuous
Operating Temperature Range		$-55^{\circ}C$ to $+125^{\circ}C$	$0^{\circ}C$ to $+70^{\circ}C$
Maximum Junction Temperature		$150^{\circ}C$	$100^{\circ}C$
Storage Temperature Range		$-65^{\circ}C$ to $+150^{\circ}C$	$-65^{\circ}C$ to $+150^{\circ}C$
Lead Temperature (Soldering, 10 seconds)		$260^{\circ}C$	$260^{\circ}C$
Thermal Resistance (θ_{JA}) ⁽⁴⁾	CDIP (NFE)	Pd	900 mW
		θ_{JA}	$100^{\circ}C/W$
	SOIC (D)	θ_{JA}	$115^{\circ}C/W$
		Pd	500 mW
	PDIP (N)	θ_{JA}	$90^{\circ}C/W$
Soldering Information	Dual-In-Line Package	Soldering (10 seconds)	$+260^{\circ}C$
		Vapor Phase (60 seconds)	$+215^{\circ}C$
		Infrared (15 seconds)	$+220^{\circ}C$

- (1) Refer to RETS146X for LM146J military specifications.
- (2) For supply voltages less than $\pm 15V$, the absolute maximum input voltage is equal to the supply voltage.
- (3) If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/ Distributors for availability and specifications.
- (4) The maximum power dissipation for these devices must be derated at elevated temperatures and is dictated by T_{jMAX} , θ_{jA} , and the ambient temperature, T_A . The maximum available power dissipation at any temperature is $P_d = (T_{jMAX} - T_A) / \theta_{jA}$ or the $25^\circ C$ P_{dMAX} , whichever is less.
- (5) Any of the amplifier outputs can be shorted to ground indefinitely; however, more than one should not be simultaneously shorted as the maximum junction temperature will be exceeded.

DC ELECTRICAL CHARACTERISTICS

($V_S = \pm 15V$, $I_{SET} = 10 \mu A$)⁽¹⁾

Parameter	Conditions	LM146			LM346			Units
		Min	Typ	Max	Min	Typ	Max	
Input Offset Voltage	$V_{CM} = 0V$, $R_S \leq 50\Omega$, $T_A = 25^\circ C$		0.5	5		0.5	6	mV
Input Offset Current	$V_{CM} = 0V$, $T_A = 25^\circ C$		2	20		2	100	nA
Input Bias Current	$V_{CM} = 0V$, $T_A = 25^\circ C$		50	100		50	250	nA
Supply Current (4 Op Amps)	$T_A = 25^\circ C$		1.4	2.0		1.4	2.5	mA
Large Signal Voltage Gain	$R_L = 10 k\Omega$, $\Delta V_{OUT} = \pm 10V$, $T_A = 25^\circ C$	100	1000		50	1000		V/mV
Input CM Range	$T_A = 25^\circ C$	± 13.5	± 14		± 13.5	± 14		V
CM Rejection Ratio	$R_S \leq 10 k\Omega$, $T_A = 25^\circ C$	80	100		70	100		dB
Power Supply Rejection Ratio	$R_S \leq 10 k\Omega$, $T_A = 25^\circ C$, $V_S = \pm 5$ to $\pm 15V$	80	100		74	100		dB
Output Voltage Swing	$R_L \geq 10 k\Omega$, $T_A = 25^\circ C$	± 12	± 14		± 12	± 14		V
Short-Circuit	$T_A = 25^\circ C$	5	20	35	5	20	35	mA
Gain Bandwidth Product	$T_A = 25^\circ C$	0.8	1.2		0.5	1.2		MHz
Phase Margin	$T_A = 25^\circ C$		60			60		Deg
Slew Rate	$T_A = 25^\circ C$		0.4			0.4		V/μs
Input Noise Voltage	$f = 1$ kHz, $T_A = 25^\circ C$		28			28		$8 \text{ nV}/\sqrt{\text{Hz}}$
Channel Separation	$R_L = 10 k\Omega$, $\Delta V_{OUT} = 0V$ to $\pm 12V$, $T_A = 25^\circ C$		120			120		dB
Input Resistance	$T_A = 25^\circ C$		1.0			1.0		MΩ
Input Capacitance	$T_A = 25^\circ C$		2.0			2.0		pF
Input Offset Voltage	$V_{CM} = 0V$, $R_S \leq 50\Omega$		0.5	6		0.5	7.5	mV
Input Offset Current	$V_{CM} = 0V$		2	25		2	100	nA
Input Bias Current	$V_{CM} = 0V$		50	100		50	250	nA
Supply Current (4 Op Amps)			1.7	2.2		1.7	2.5	mA
Large Signal Voltage Gain	$R_L = 10 k\Omega$, $\Delta V_{OUT} = \pm 10V$	50	1000		25	1000		V/mV
Input CM Range		± 13.5	± 14		± 13.5	± 14		V
CM Rejection Ratio	$R_S \leq 50\Omega$	70	100		70	100		dB
Power Supply Rejection Ratio	$R_S \leq 50\Omega$, $V_S = \pm 5V$ to $\pm 15V$	76	100		74	100		dB
Output Voltage Swing	$R_L \geq 10 k\Omega$	± 12	± 14		± 12	± 14		V

(1) These specifications apply over the absolute maximum operating temperature range unless otherwise noted.

DC ELECTRICAL CHARACTERISTIC

($V_S = \pm 15V$, $I_{SET} = 10 \mu A$)

Parameter	Conditions	LM146			LM346			Units
		Min	Typ	Max	Min	Typ	Max	
Input Offset Voltage	$V_{CM} = 0V$, $R_S \leq 50\Omega$, $T_A = 25^\circ C$		0.5	5		0.5	7	mV
Input Bias Current	$V_{CM} = 0V$, $T_A = 25^\circ C$		7.5	20		7.5	100	nA
Supply Current (4 Op Amps)	$T_A = 25^\circ C$		140	250		140	300	μA
Gain Bandwidth Product	$T_A = 25^\circ C$	80	100		50	100		kHz

DC ELECTRICAL CHARACTERISTICS(V_S=±1.5V, I_{SET}=10 µA)

Parameter	Conditions	LM146			LM346			Units
		Min	Typ	Max	Min	Typ	Max	
Input Offset Voltage	V _{CM} =0V, R _S ≤50Ω, T _A =25°C		0.5	5		0.5	7	mV
Input CM Range	T _A =25°C	±0.7			±0.7			V
CM Rejection Ratio	R _S ≤50Ω, T _A =25°C		80			80		dB
Output Voltage Swing	R _L ≥10 kΩ, T _A =25°C	±0.6			±0.6			V

TYPICAL PERFORMANCE CHARACTERISTICS

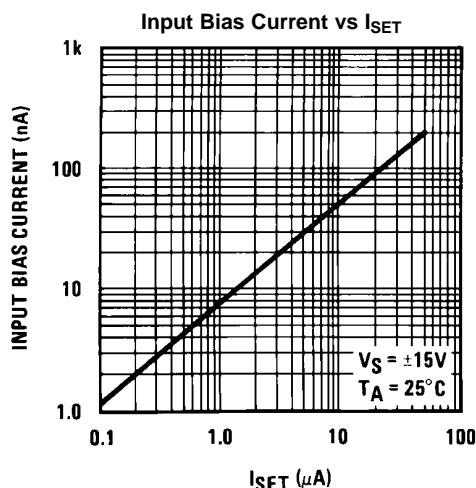


Figure 2.

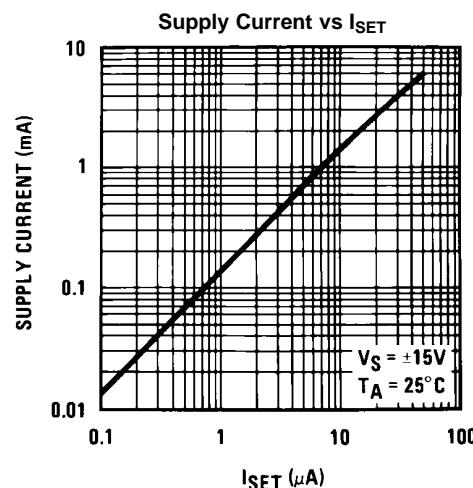


Figure 3.

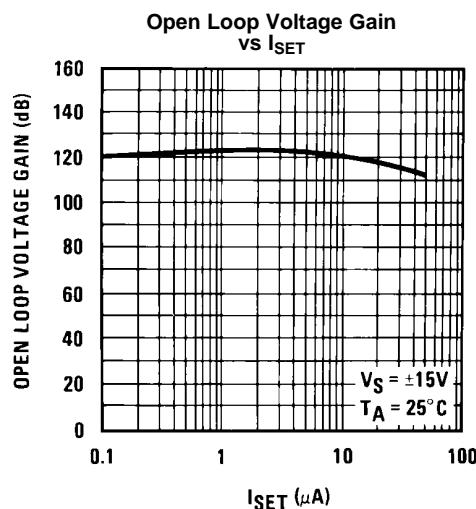


Figure 4.

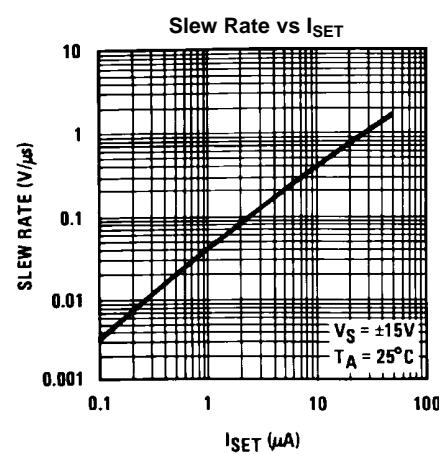


Figure 5.

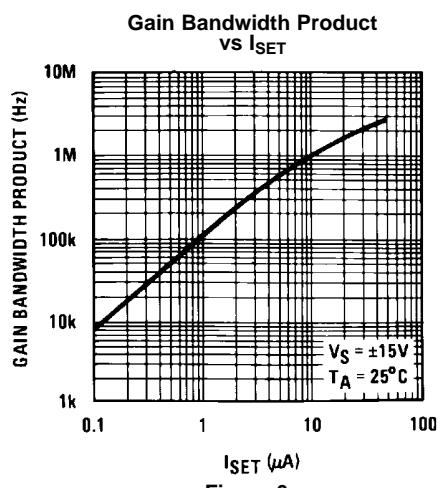


Figure 6.

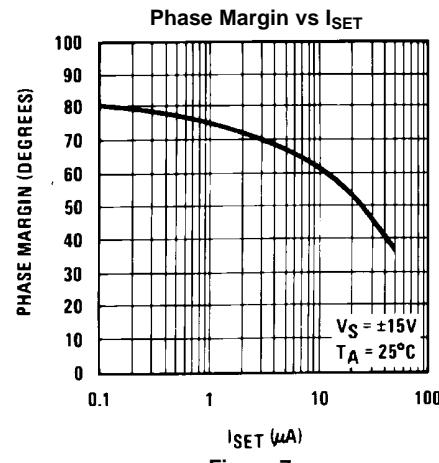


Figure 7.

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

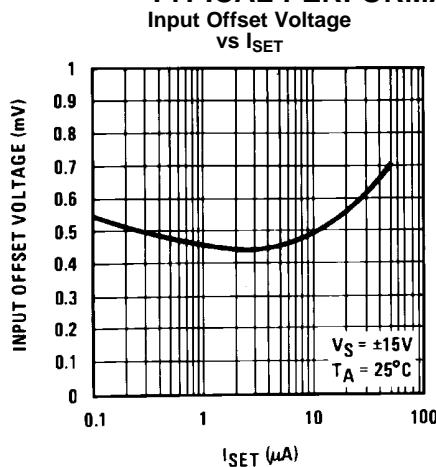


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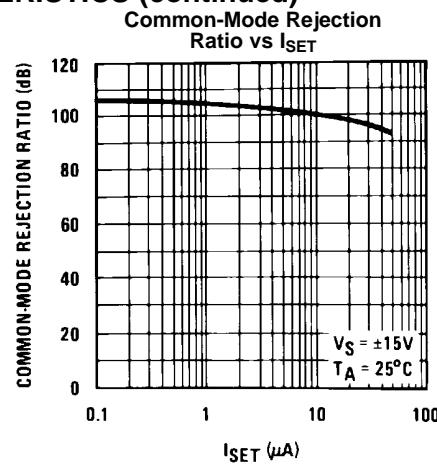


Figure 9.

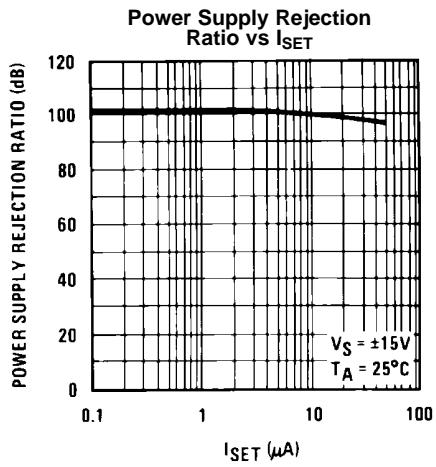


Figure 10.

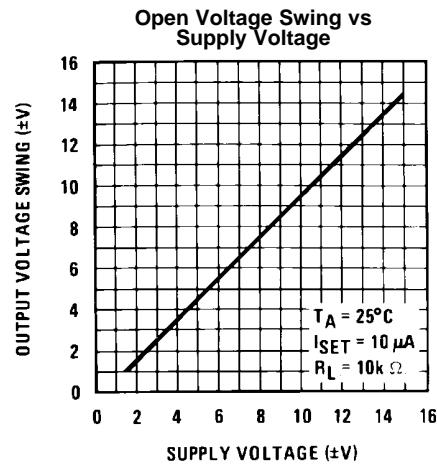


Figure 11.

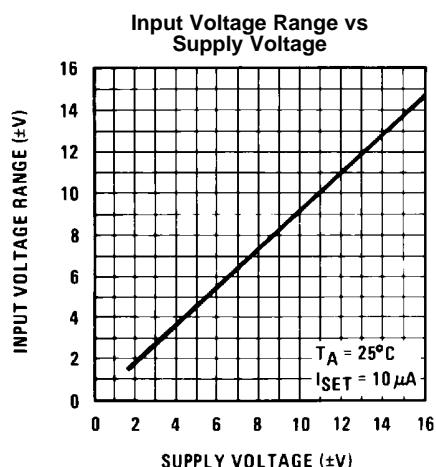


Figure 12.

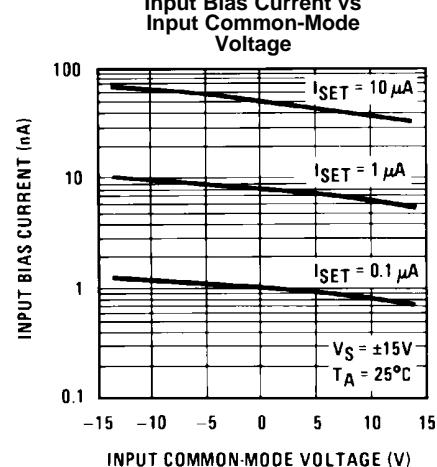
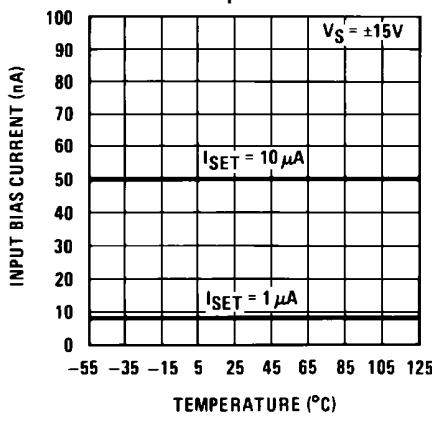
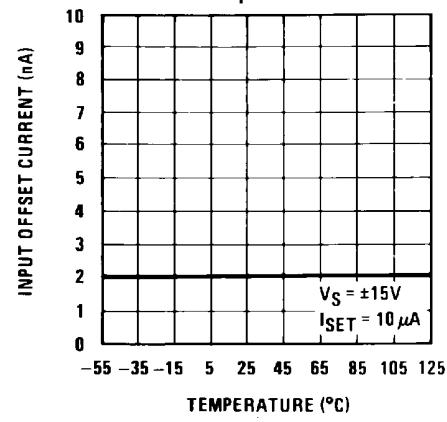
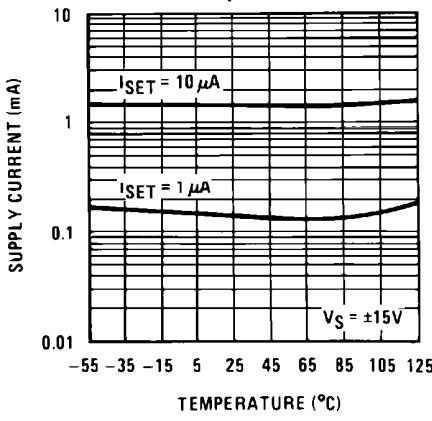
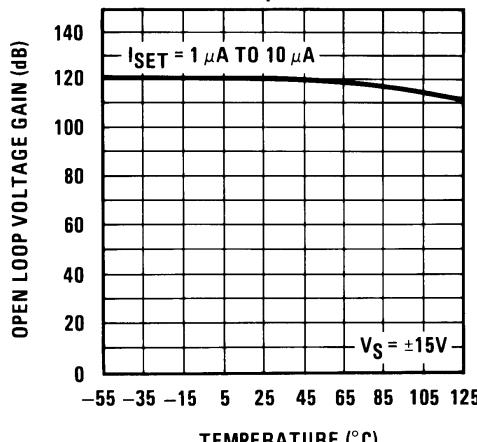
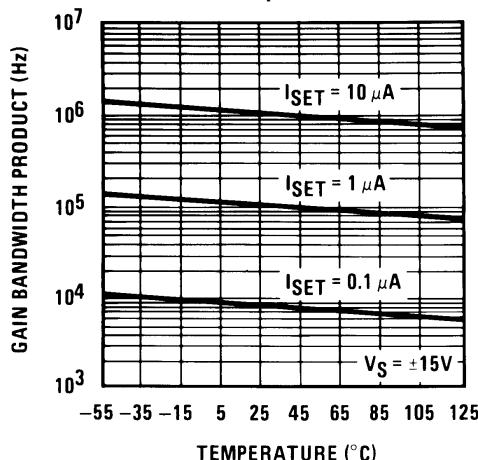
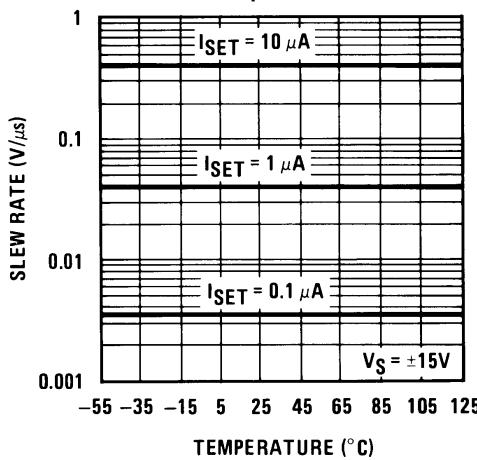


Figure 13.

TYPICAL PERFORMANCE CHARACTERISTICS (continued)
**Input Bias Current vs
Temperature**

Figure 14.
**Input Offset Current vs
Temperature**

Figure 15.
**Supply Current vs
Temperature**

Figure 16.
**Open Loop Voltage Gain
vs Temperature**

Figure 17.
**Gain Bandwidth Product
vs Temperature**

Figure 18.
**Slew Rate vs
Temperature**

Figure 19.

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

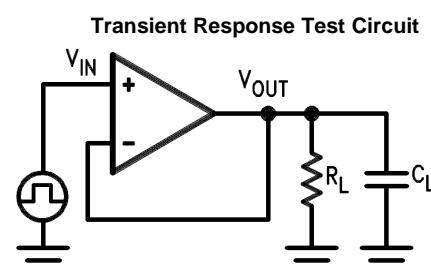
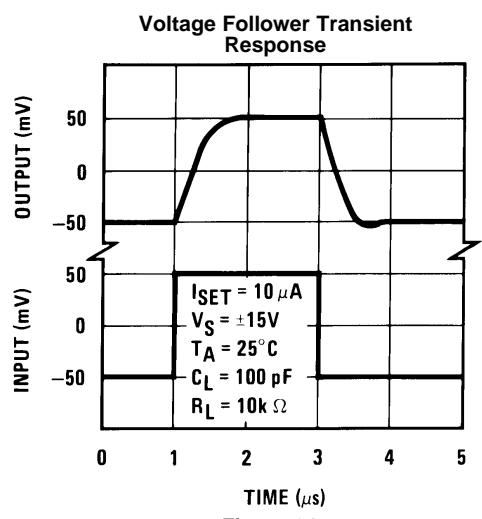
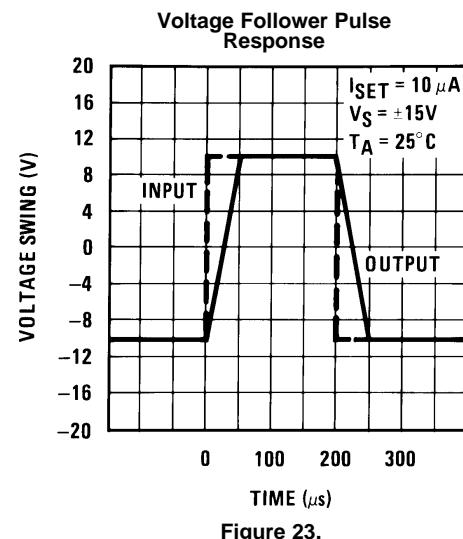
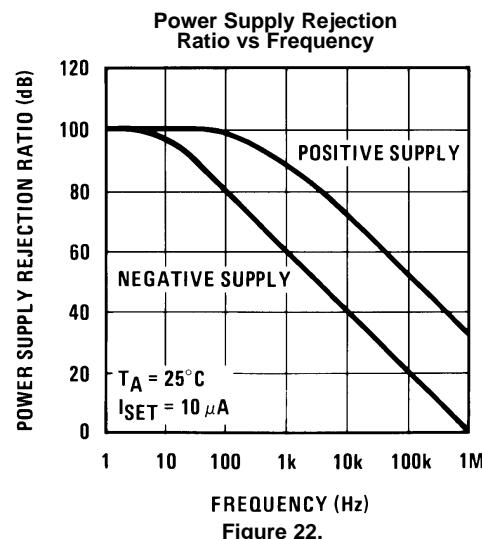
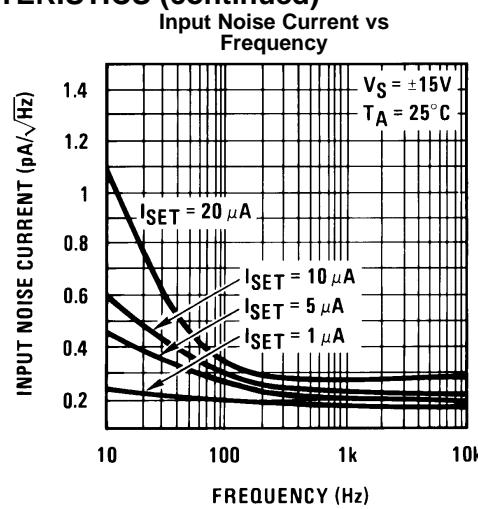
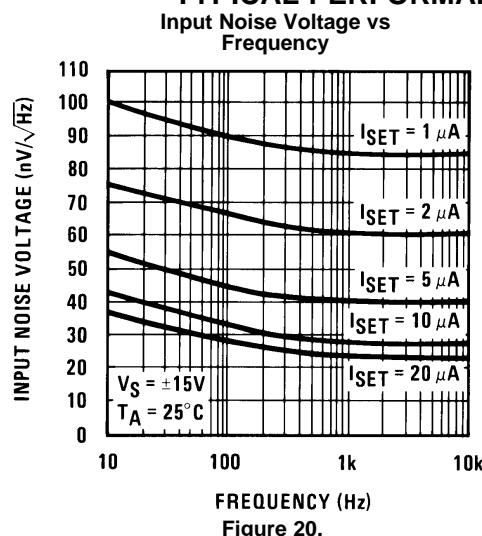


Figure 25.

APPLICATION HINTS

Avoid reversing the power supply polarity; the device will fail.

COMMON-MODE INPUT VOLTAGE

The negative common-mode voltage limit is one diode drop above the negative supply voltage. Exceeding this limit on either input will result in an output phase reversal. The positive common-mode limit is typically 1V below the positive supply voltage. No output phase reversal will occur if this limit is exceeded by either input.

OUTPUT VOLTAGE SWING VS I_{SET}

For a desired output voltage swing the value of the minimum load depends on the positive and negative output current capability of the op amp. The maximum available positive output current, (I_{CL+}), of the device increases with I_{SET} whereas the negative output current (I_{CL-}) is independent of I_{SET} . [Figure 26](#) illustrates the above.

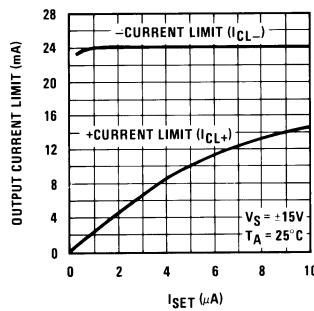


Figure 26. Output Current Limit vs I_{SET}

INPUT CAPACITANCE

The input capacitance, C_{IN} , of the LM146 is approximately 2 pF; any stray capacitance, C_S , (due to external circuit layout) will add to C_{IN} . When resistive or active feedback is applied, an additional pole is added to the open loop frequency response of the device. For instance with resistive feedback ([Figure 27](#)), this pole occurs at $\frac{1}{2}\pi (R1||R2)(C_{IN} + C_S)$. Make sure that this pole occurs at least 2 octaves beyond the expected -3 dB frequency corner of the closed loop gain of the amplifier; if not, place a lead capacitor in the feedback such that the time constant of this capacitor and the resistance it parallels is equal to the $R_i(C_S + C_{IN})$, where R_i is the input resistance of the circuit.

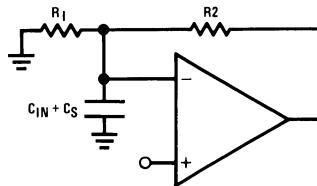


Figure 27. Resistive Feedback Circuit Example

TEMPERATURE EFFECT ON THE GBW

The GBW (gain bandwidth product), of the LM146 is directly proportional to I_{SET} and inversely proportional to the absolute temperature. When using resistors to set the bias current, I_{SET} , of the device, the GBW product will decrease with increasing temperature. Compensation can be provided by creating an I_{SET} current directly proportional to temperature (see [Typical Applications](#)).

ISOLATION BETWEEN AMPLIFIERS

The LM146 die is isothermally layed out such that crosstalk between *all* 4 amplifiers is in excess of -105 dB (DC). Optimum isolation (better than -110 dB) occurs between amplifiers A and D, B and C; that is, if amplifier A dissipates power on its output stage, amplifier D is the one which will be affected the least, and vice versa. Same argument holds for amplifiers B and C.

LM146 TYPICAL PERFORMANCE SUMMARY

The LM146 typical behaviour is shown in [Figure 28](#). The device is fully predictable. As the set current, I_{SET} , increases, the speed, the bias current, and the supply current increase while the noise power decreases proportionally and the V_{OS} remains constant. The usable GBW range of the op amp is 10 kHz to 3.5–4 MHz.

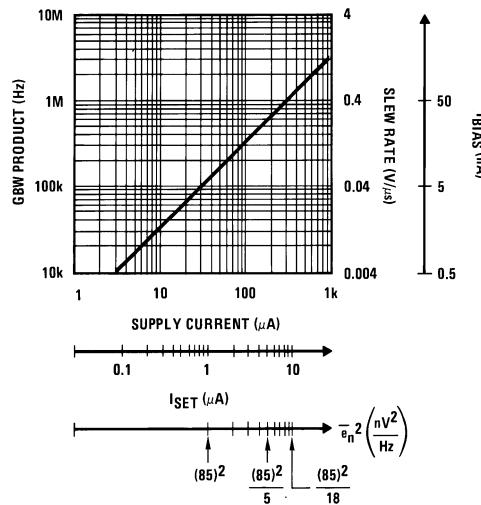


Figure 28. LM146 Typical Characteristics

Low Power Supply Operation: The quad op amp operates down to ± 1.3 V supply. Also, since the internal circuitry is biased through programmable current sources, no degradation of the device speed will occur.

SPEED VS POWER CONSUMPTION

LM146 vs LM4250 (single programmable). Through [Figure 29](#), we observe that the LM146's power consumption has been optimized for GBW products above 200 kHz, whereas the LM4250 will reach a GBW of no more than 300 kHz. For GBW products below 200 kHz, the LM4250 will consume less power.

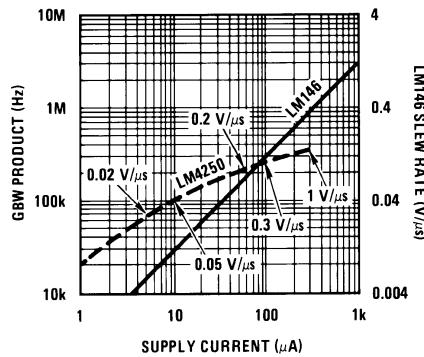
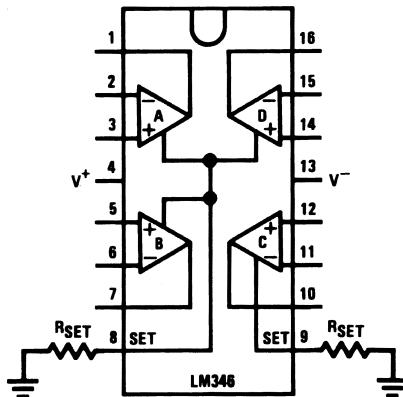


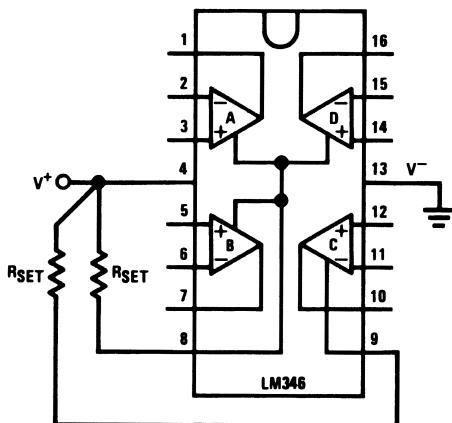
Figure 29. LM146 vs LM4250

Typical Applications



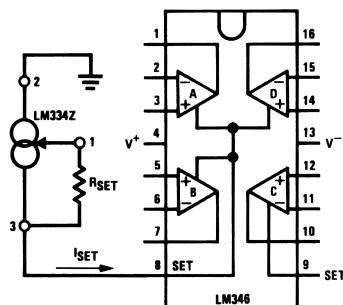
$$I_{SET} \approx \frac{|V_-| - 0.6V}{R_{SET}}$$

Figure 30. Dual Supply or Negative Supply Biasing



$$I_{SET} \approx \frac{V_+ - 0.6V}{R_{SET}}$$

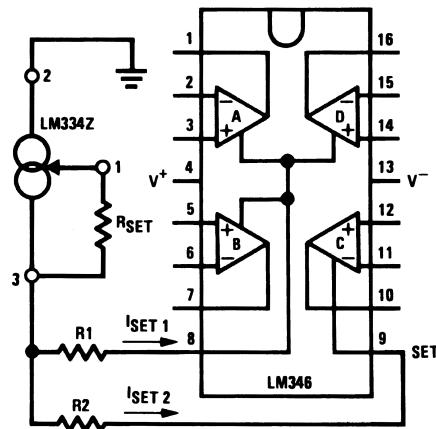
Figure 31. Single (Positive) Supply Biasing



$$I_{SET} = \frac{67.7 \text{ mV}}{R_{SET}}$$

- The LM334 provides an I_{SET} directly proportional to absolute temperature. This cancels the slight GBW product Temperature coefficient of the LM346.

Figure 32. Current Source Biasing with Temperature Compensation



$$\frac{I_{SET1}}{I_{SET2}} = \frac{R_2}{R_1}, \quad I_{SET1} + I_{SET2} = \frac{67.7 \text{ mV}}{R_{SET}}$$

- For $I_{SET1} \approx I_{SET2}$ resistors R1 and R2 are not required if a slight error between the 2 set currents can be tolerated. If not, then use $R1 = R2$ to create a 100 mV drop across these resistors.

Figure 33. Biasing all 4 Amplifiers with Single Current Source

Active Filters Applications

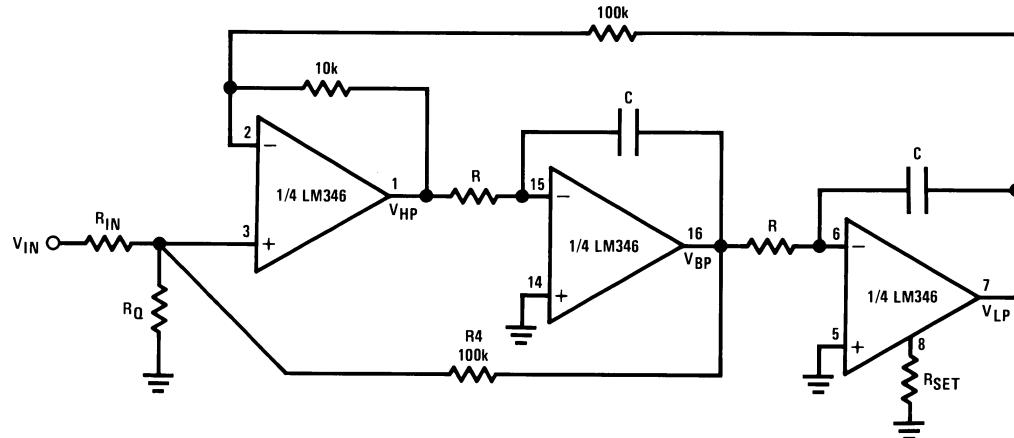


Figure 34. Basic (Non-Inverting “State Variable”) Active Filter Building Block

- The LM146 quad programmable op amp is especially suited for active filters because of their adequate GBW product and low power consumption.

Circuit synthesis equations (for circuit analysis equations, consult with the LM146 data sheet).

Need to know desired: f_o = center frequency measured at the BP output

Q_o = quality factor measured at the BP output

H_o = gain at the output of interest (BP or HP or LP or all of them)

- Relation between different gains: $H_o(BP) = 0.316 \times Q_o \times H_o(LP)$; $H_o(LP) = 10 \times H_o(HP)$

$$\bullet R \times C = \frac{5.033 \times 10^{-2}}{f_o} \text{ (sec)}$$

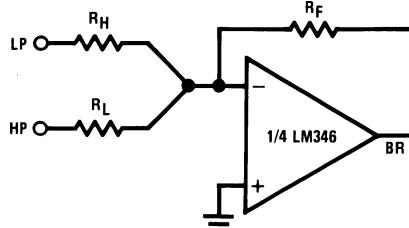
$$\bullet \text{For BP output: } R_Q = \left(\frac{3.478 Q_o - H_o(BP)}{10^5} - \frac{H_o(BP)}{10^5 \times 3.748 \times Q_o} \right)^{-1}; R_{IN} = \frac{\left(\frac{3.478 Q_o}{H_o(BP)} - 1 \right)}{\frac{1}{R_Q} + 10^{-5}}$$

$$\bullet \text{For HP output: } R_Q = \frac{1.1 \times 10^5}{3.478 Q_o (1.1 - H_o(HP)) - H_o(HP)}; R_{IN} = \frac{\frac{1.1}{H_o(HP)} - 1}{\frac{1}{R_Q} + 10^{-5}}$$

$$\bullet \text{For LP output: } R_Q = \frac{11 \times 10^5}{3.478 Q_o (11 - H_o(LP)) - H_o(LP)}; R_{IN} = \frac{\frac{11}{H_o(LP)} - 1}{\frac{1}{R_Q} + 10^{-5}}$$

- For BR (notch) output: Use the 4th amplifier of the LM146 to sum the LP and HP outputs of the basic filter.

Note. All resistor values are given in ohms.



$$\sqrt{\frac{R_H}{R_L}} = 0.316 \frac{f_{notch}}{f_o}$$

$$\text{Determine } R_F \text{ according to the desired gains: } H_o(BR) \Big|_{f < f_{\text{notch}}} = \frac{R_F}{R_L} H_o(LP), \quad H_o(BR) \Big|_{f > f_{\text{notch}}} = \frac{R_F}{R_H} H_o(HP)$$

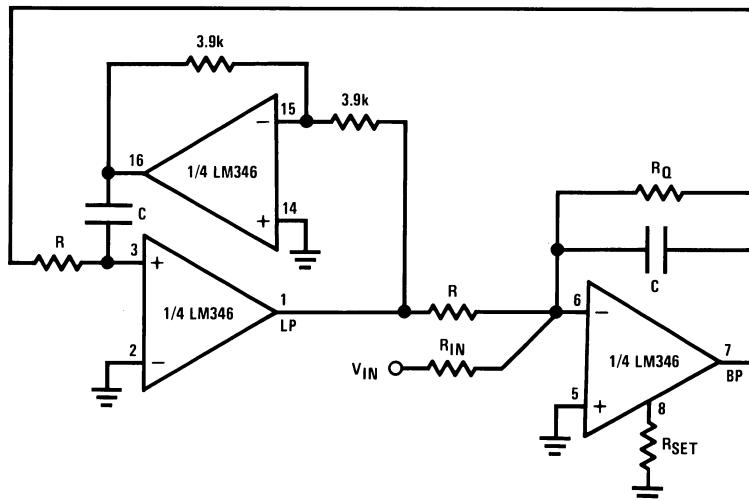
- **Where to use amplifier C:** Examine the above gain relations and determine the dynamics of the filter. Do not allow slew rate limiting in any output (V_{HP} , V_{BP} , V_{LP}), that is:

$$V_{IN(\text{peak})} < 63.66 \times 10^3 \times \frac{I_{SET}}{10 \mu\text{A}} \times \frac{1}{f_o \times H_o} \text{ (Volts)}$$

If necessary, use amplifier C, biased at higher I_{SET} , where you get the largest output swing.

Deviation from Theoretical Predictions: Due to the finite GBW products of the op amps the f_o , Q_o will be slightly different from the theoretical predictions.

$$f_{\text{real}} \approx \frac{f_o}{1 + \frac{2 f_o}{\text{GBW}}}, \quad Q_{\text{real}} \approx \frac{Q_o}{1 - \frac{3.2 f_o \times Q_o}{\text{GBW}}}$$



- If resistive biasing is used to set the LM346 performance, the Q_o of this filter building block is nearly insensitive to the op amp's GBW product temperature drift; it has also better noise performance than the state variable filter.

Figure 35. A Simple-to-Design BP, LP Filter Building Block

Circuit Synthesis Equations

$$H_o(BP) = Q_o H_o(LP); \quad R \times C = \frac{0.159}{f_o}; \quad R_Q = Q_o \times R; \quad R_{IN} = \frac{R_Q}{H_o(BP)} = \frac{R}{H_o(LP)}$$

- For the eventual use of amplifier C, see comments above. (2)

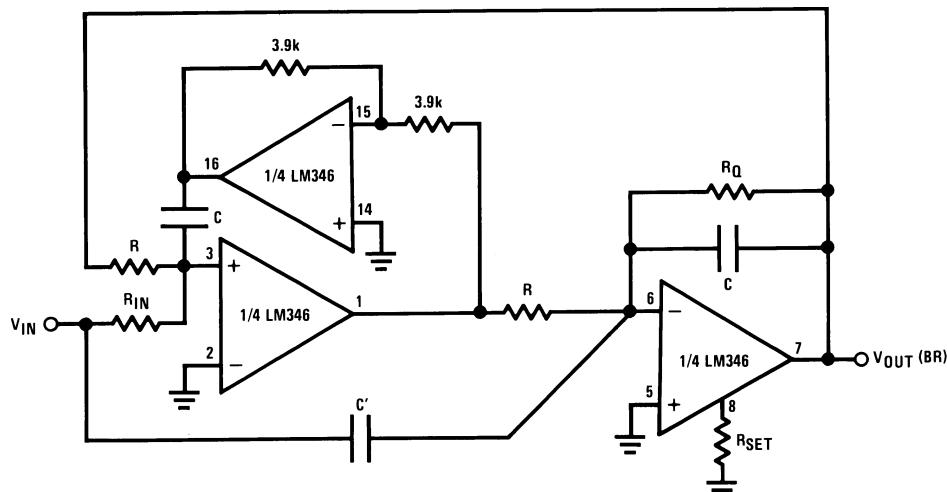


Figure 36. A 3-Amplifier Notch Filter (or Elliptic Filter Building Block)

Circuit Synthesis Equations

$$R \times C = \frac{0.159}{f_o}; R_o = Q_o \times R; R_{IN} = \frac{0.159 \times f_o}{C' \times f_{notch}^2}$$

$$H_o(BR) \Big|_{f < f_{notch}} = \frac{R}{R_{IN}} H_o(BR) \Big|_{f > f_{notch}} = \frac{C'}{C}$$

• For nothing but a notch output: $R_{IN} = R$, $C' = C$. (3)

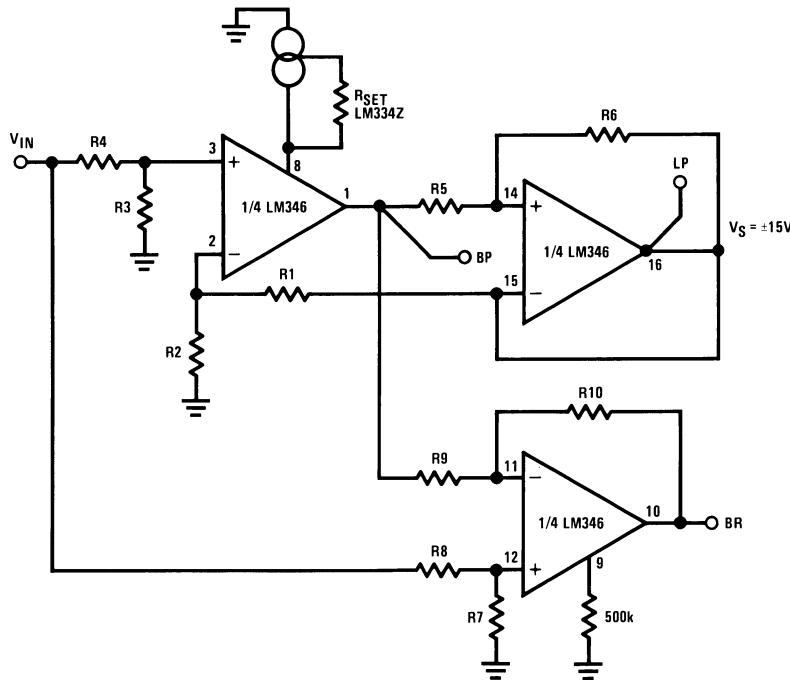
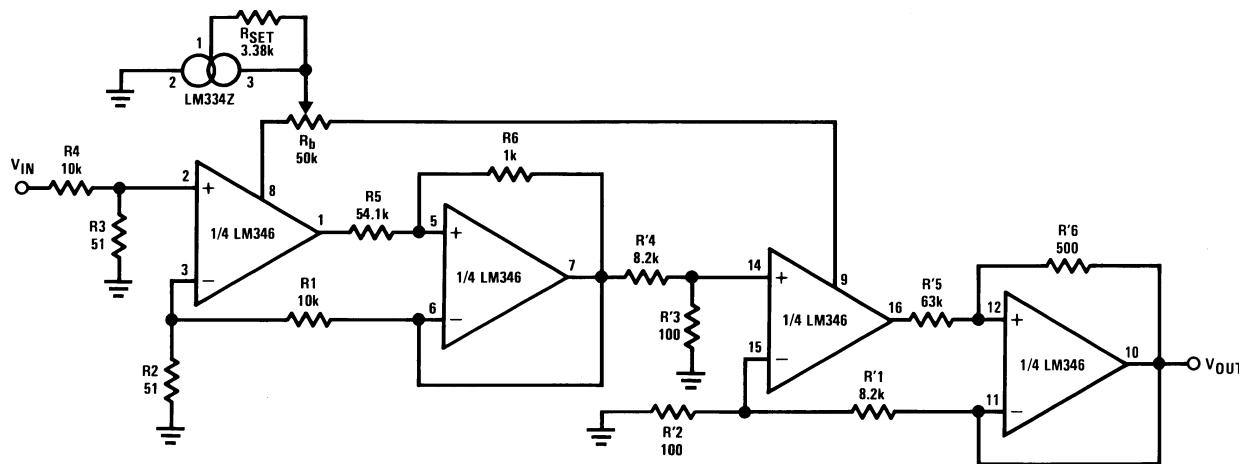


Figure 37. Capacitorless Active Filters (Basic Circuit)

- This is a BP, LP, BR filter. The filter characteristics are created by using the tunable frequency response of the LM346.
- **Limitations:** $Q_o < 10$, $f_o \times Q_o < 1.5$ MHz, output voltage should not exceed $V_{peak(out)} \leq \frac{63.66 \times 10^3}{f_o} \times \frac{|I_{SET}(\mu A)|}{10 \mu A}$ (V)
- Design equations: $a = \frac{R6 + R5}{R6}$, $b = \frac{R2}{R1 + R2}$, $c = \frac{R3}{R3 + R4}$, $d = \frac{R7}{R8 + R7}$, $e = \frac{R10}{R9 + R10}$, $f_o(BP) = f_u \sqrt{\frac{b}{a}}$, $H_o(BP) = a \times c$, $H_o(LP) = \frac{c}{b}$, $Q_o = \sqrt{a \times b}$
 $f_o(BR) = f_o(BP) \left(1 - \frac{c}{b} \right) \approx f_o(BP)$ ($C < < 1$) provided that $d = H_o(BP) \times e$, $H_o(BR) = \frac{R10}{R9}$.
- Advantage: $f_o Q_o$, H_o can be independently adjusted; that is, the filter is extremely easy to tune.
- Tuning procedure (ex. BP tuning)
 1. Pick up a convenient value for b ; ($b < 1$)
 2. Adjust Q_o through $R5$
 3. Adjust $H_o(BP)$ through $R4$
 4. Adjust f_o through R_{SET} . This adjusts the unity gain frequency (f_u) of the op amp.

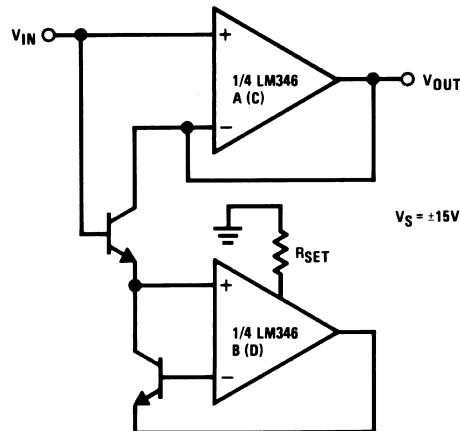


Ex: $f_c = 20$ kHz, H_0 (gain of the filter) = 1, $Q_{01} = 0.541$, $Q_{02} = 1.306$.

- Since for this filter the GBW product of all 4 amplifiers has been designed to be the same (~1 MHz) only one current source can be used to bias the circuit. Fine tuning can be further accomplished through R_b .

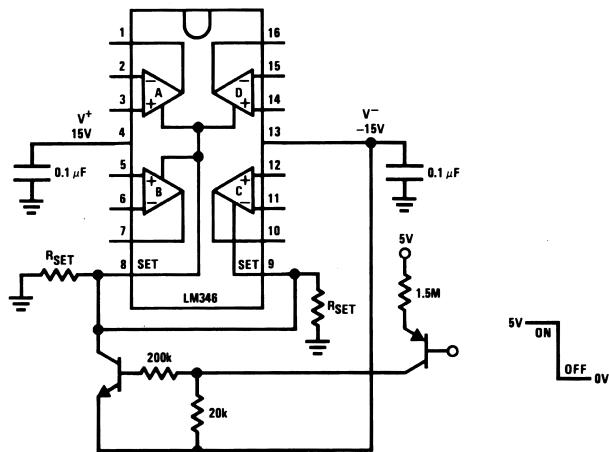
Figure 38. A 4th Order Butterworth Low Pass Capacitorless Filter

Miscellaneous Applications



- For better performance, use a matched NPN pair.

Figure 39. A Unity Gain Follower with Bias Current Reduction



- By pulling the SET pin(s) to V^- the op amp(s) shuts down and its output goes to a high impedance state. According to this property, the LM346 can be used as a very low speed analog switch.

Figure 40. Circuit Shutdown

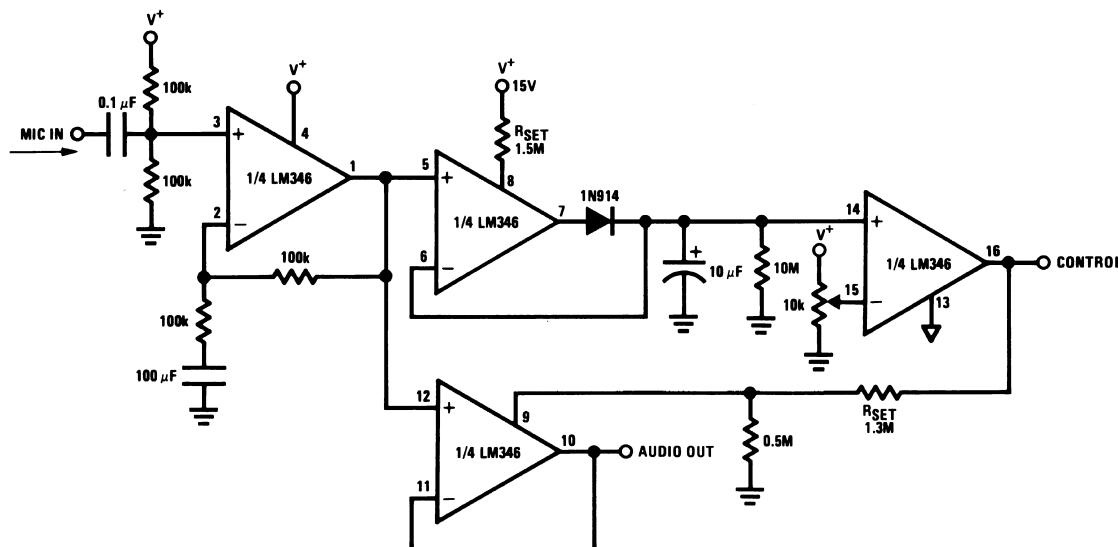
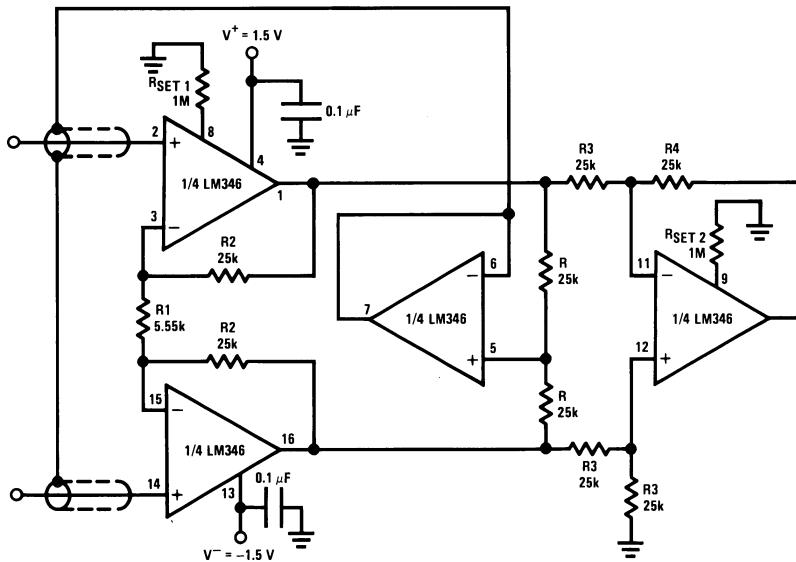


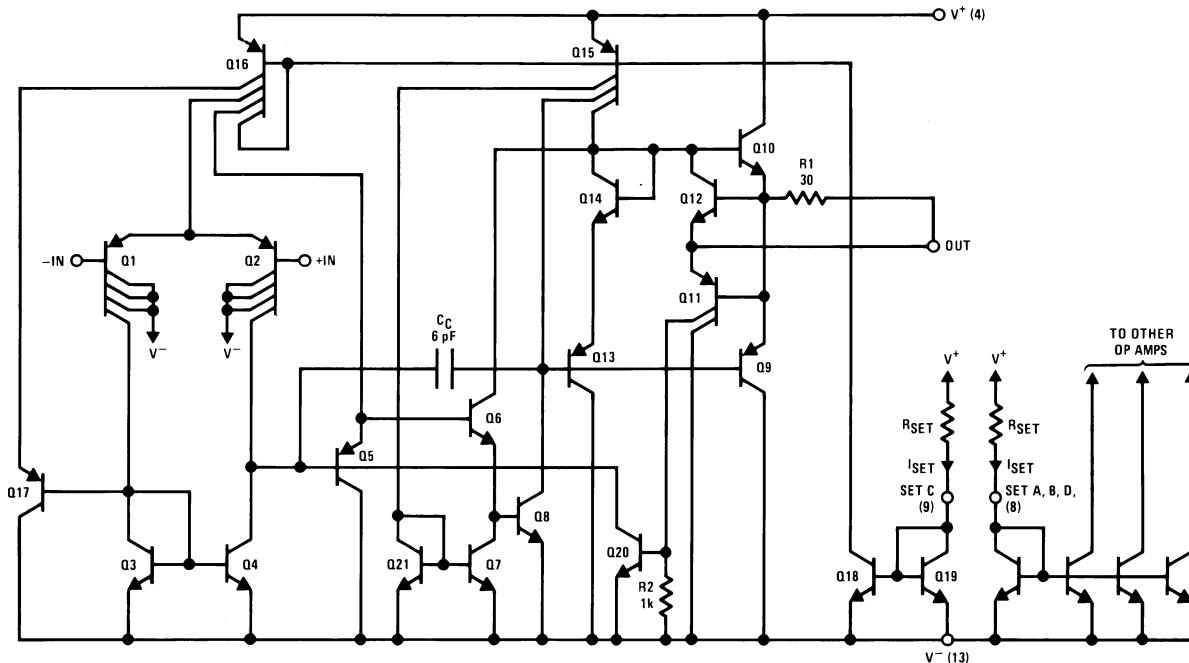
Figure 41. Voice Activated Switch and Amplifier



- CMRR: 100 dB (typ)
- Power dissipation: 0.4 mW

Figure 42. x10 Micropower Instrumentation Amplifier with Buffered Input Guarding

Schematic Diagram



PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LM346M/NOPB	ACTIVE	SOIC	D	16	48	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	0 to 70	LM346M	Samples
LM346MX/NOPB	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	0 to 70	LM346M	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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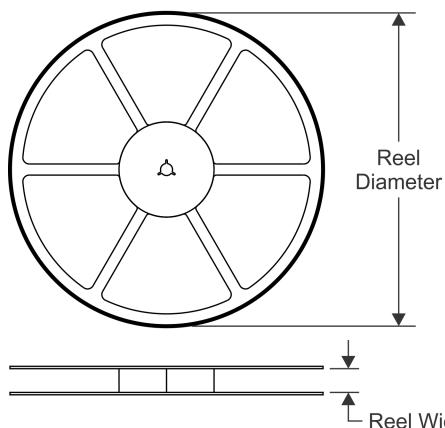
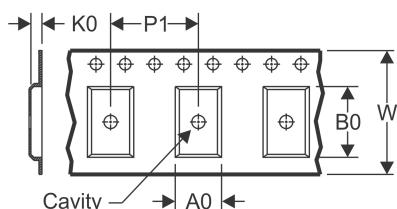


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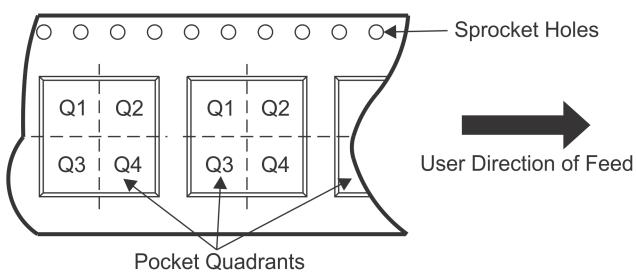
PACKAGE OPTION ADDENDUM

25-Feb-2015

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

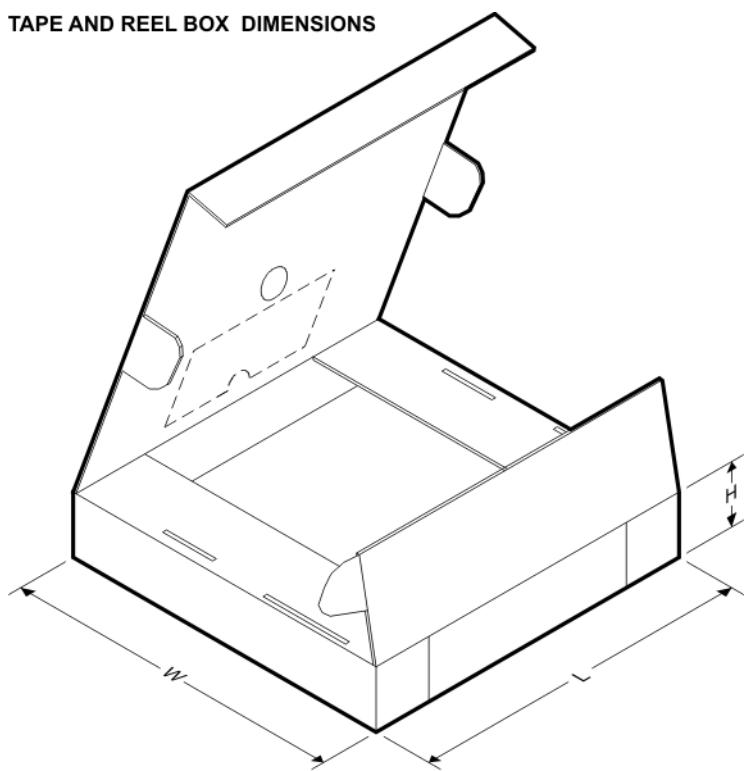
TAPE AND REEL INFORMATION
REEL DIMENSIONS

TAPE DIMENSIONS


A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LM346MX/NOPB	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.3	8.0	16.0	Q1

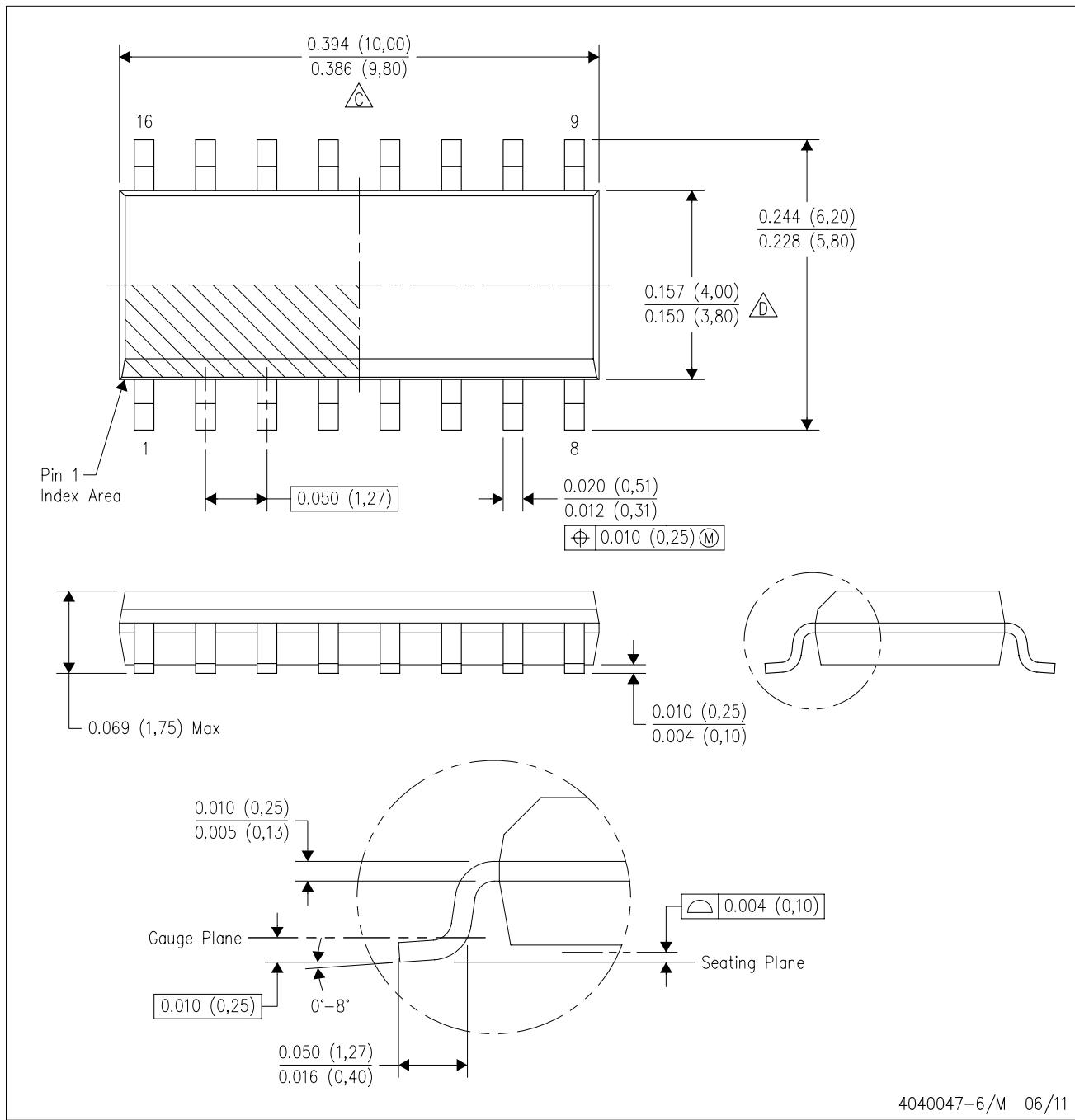
TAPE AND REEL BOX DIMENSIONS

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LM346MX/NOPB	SOIC	D	16	2500	367.0	367.0	35.0

D (R-PDSO-G16)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.

D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.

E. Reference JEDEC MS-012 variation AC.

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